



TR BD129;CEMI;TO126;tranzystor; NPN;0.5A;400V;17.5W



Dane techniczne:

Nazwa: BD129

Typ tranzystora: bipolarny

Kierunek przewodnictwa: NPN

Prąd kolektora: 0.5A

Napięcie kolektor-emiter: 400V

Moc: 17.5W

Obudowa: TO126

Montaż: przewlekany (THT)

Producent: CEMI



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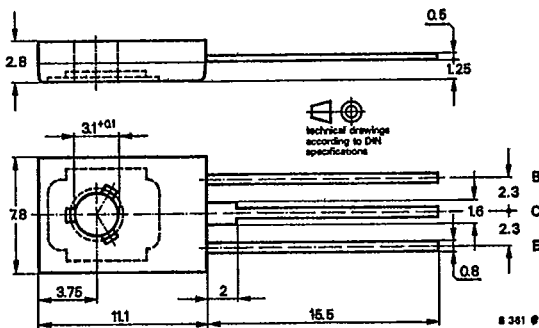
Silicon NPN Planar Power Transistors

Applications: General at high supply voltages

Features:

- High reverse voltage
- Power dissipation 17.5 W

Dimensions in mm



Collector connected with metallic surface

Standard plastic case
 12 A 3 DIN 41 869
 JEDEC TO 126 (SOT 32)
 Weight max. 0.8 g

Accessories

- Isolating washer No. 119880
- Washer 3.2 DIN 125A

Absolute maximum ratings

	BD 127	BD 128	BD 129	
Collector-base voltage	300	350	400	V
Collector-emitter voltage	250	300	350	V
Emitter-base voltage		5		V
Collector current		500		mA
Total power dissipation $T_{case} \leq 45^\circ C$		17.5		W
Junction temperature		150		$^\circ C$
Storage temperature range		-55 ... +150		$^\circ C$
Tightening torque		70		N cm

Maximum thermal resistance

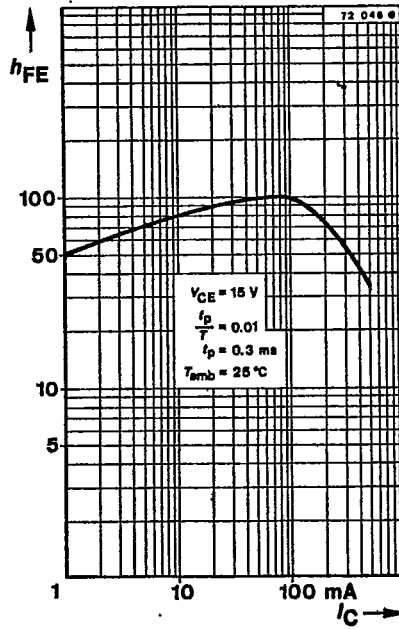
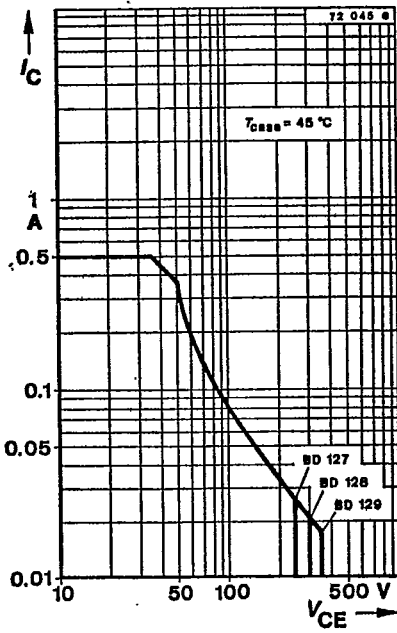
Junction case	R_{thJC}	6	K/W
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¹⁾ with screw M3 and washer 3.2 DIN 125A

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Characteristics	Min.	Typ.	Max.
$T_{amb} = 25^\circ C$, unless otherwise specified			
Collector cut-off current			
$V_{CB} = 150 V$			50 nA
$V_{CB} = 150 V, T_{amb} = 150^\circ C$			100 μA
Collector-base breakdown voltage			
$I_C = 1 \mu A$			
BD 127	$V_{(BR)CBO}$	300	V
BD 128	$V_{(BR)CBO}$	350	V
BD 129	$V_{(BR)CBO}$	400	V
Collector-emitter breakdown voltage			
$I_C = 1 mA$			
BD 127	$V_{(BR)CEO}^{1)}$	250	V
BD 128	$V_{(BR)CEO}^{1)}$	300	V
BD 129	$V_{(BR)CEO}^{1)}$	350	V
Emitter-base breakdown voltage			
$I_E = 1 \mu A$	$V_{(BR)EBO}$	5	V
DC forward current transfer ratio			
$V_{CE} = 15 V, I_C = 1 mA$	$h_{FE1)}$	50	
$V_{CE} = 15 V, I_C = 50 mA$	h_{FE}	30	



¹⁾ $\frac{t_p}{T} = 0.01, t_p = 0.3 ms$